

## Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application.

### Listing of Claims:

1. (currently amended): A method of sputtering a tungsten ~~or tungsten-~~  
~~containing~~ film from a tungsten target onto a semiconductor wafer including  
using krypton or xenon as a sputter gas, wherein the resistivity of the tungsten  
film is less than  $11\mu\text{ohm cm}$ .

2. (currently amended): A method as claimed in claim 1 wherein the  
deposition takes place in a vacuum chamber with a krypton pressure of less  
than 10mTorr ~~10mT~~.

3. (currently amended): A method as claimed in claim 2 wherein  
krypton pressure is less than 6mTorr ~~6mT~~.

4. (cancelled)

5. (currently amended): A method of sputtering a tungsten ~~or tungsten-~~  
~~containing~~ film from a tungsten target onto a semiconductor wafer including  
using krypton or xenon as a sputter gas, wherein the power supplied to the  
target is greater than about  $3.5\text{ watts per cm}^2$ .

6. (currently amended): A method of sputtering a tungsten ~~or tungsten-~~  
~~containing~~ film from a tungsten target onto a semiconductor wafer including  
using krypton or xenon as a sputter gas, wherein the wafer is placed on a platen  
during deposition and the platen temperature is between  $200^{\circ}\text{C}$  and  $400^{\circ}\text{C}$ .

7. (previously presented): A method of sputtering a tungsten or tungsten-containing film from a tungsten target onto a semiconductor wafer including using krypton or xenon as a sputter gas, wherein the platen is negatively DC biased.

8. (cancelled)

9. (previously presented): A method as claimed in claim 1 wherein the sputter gases further include argon.

10. (previously presented): A method as claimed in claim 9 wherein the ratio of argon to krypton or xenon is selected to minimize stress in the deposited film.

11. (previously presented): A method of forming a tungsten/tungsten nitride stack on a wafer including sputtering a tungsten nitride film on a wafer and sputtering a tungsten film on the tungsten nitride film wherein the two sputtering processes are performed in a single chamber using a single target, wherein the wafer is on a platen and the platen temperature is maintained substantially the same for the two sputter processes.

12. (cancelled)

13. (currently amended): A method of forming a tungsten/tungsten nitride stack on a wafer including sputtering a tungsten nitride film on a wafer and sputtering a tungsten film on the tungsten nitride film wherein the two sputtering processes are performed in a single chamber using a single target, wherein the tungsten film is sputtered from a tungsten target onto a semiconductor wafer including using krypton or xenon as a sputter gas in both of the two sputtering processes.

14. (currently amended): A method of forming a tungsten/tungsten nitride stack on a wafer including sputtering a tungsten nitride film on a wafer and sputtering a tungsten film on the tungsten nitride film wherein the two sputtering processes are performed in a single chamber using a single target, wherein the tungsten nitride film is deposited by reactive sputtering and the sputter gases include nitrogen and krypton.

15. (previously presented): A gate structure formed by the method of claim 11.